

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

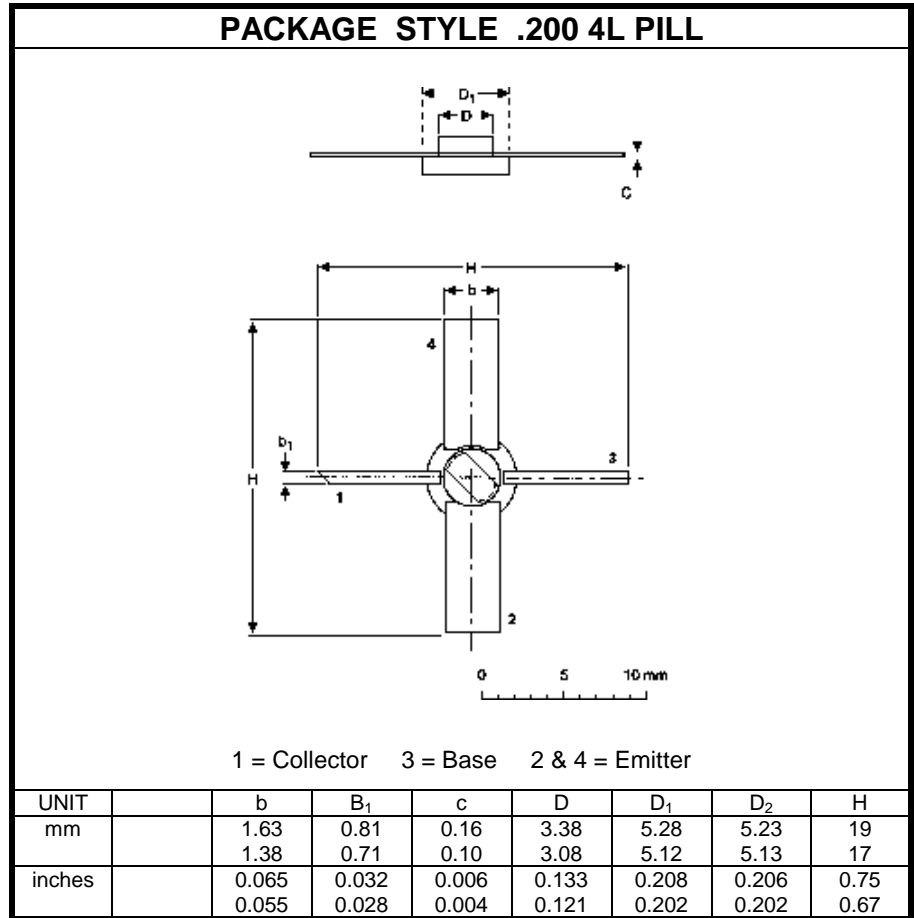
The **ASI MRW54001** is Designed for Class "A" and "AB" Amplifier Applications Up to 2.0 GHz.

FEATURES:

- **Omnigold™** Metalization System
- Implanted ballast resistors
- Common-Emitter

MAXIMUM RATINGS

I	160 mA
V_{CEO}	22 V
V_{CES}	50 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	40 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 10 mA		22			V
BV_{CES}	I _C = 10 mA		50			V
BV_{CBO}	I _C = 1.0 mA		45			V
BV_{EBO}	I _E = 250 μA		3.5			V
I_{CBO}	V _{CB} = 28 V				250	μA
h_{FE}	V _{CE} = 5.0 V	I _C = 100 mA	20		120	---
f_t	V _{CE} = 20 V	I _E = 120 mA	4.0	4.5		GHz
C_{ob}	V _{CB} = 28 V	f = 1.0 MHz			3.5	pF
G_{PE} L_G	V _{CE} = 20 V f = 2.0 GHz	I _{CQ} = 120 mA	P _{out} = 0.5 W	10		-0.2/+1.0 dB